

|    | Type | Hits   | Search Text  | DBs   |
|----|------|--------|--|---|
| 1  | BRS  | 191069 | mosfet or (metal adj oxide adj semiconductor adj (fet<br>or field)) or pmos or cmos or nmos or misfet  | USPAT; US-PGPUB; EPO;<br>JPO; DERWENT;<br>IBM_TDB |
| 2  | BRS  | 16687  | sti or shallow adj trench  | USPAT; US-PGPUB; EPO;<br>JPO; DERWENT;<br>IBM_TDB |
| 3  | BRS  | 90054  | indium   | USPAT; US-PGPUB; EPO;<br>JPO; DERWENT;<br>IBM_TDB |
| 4  | BRS  | 3      | indium near8 (corner or edge or next or adjacent\$4<br>near4 (sti or shallow adj trench)   | USPAT; US-PGPUB; EPO;<br>JPO; DERWENT;<br>IBM_TDB |
| 5  | IS&R | 8      | ((("6162679") or ("5960276") or ("6228726") or<br>("5296392") or ("6277697") or ("6245639") or<br>("6331458") or ("6504219")).PN.              | USPAT   |
| 6  | BRS  | 7      | indium near8 (sti or shallow adj trench)   | USPAT; US-PGPUB; EPO;<br>JPO; DERWENT;<br>IBM_TDB |
| 7  | BRS  | 3      | indium near8 (corner or edge or next or adjacent\$4<br>near4 (sti or shallow adj trench)   | USPAT; US-PGPUB; EPO;<br>JPO; DERWENT;<br>IBM_TDB |
| 8  | BRS  | 4      | (indium near8 (sti or shallow adj trench)) not<br>(indium near8 (corner or edge or next or<br>adjacent\$4) near4 (sti or shallow adj trench) ) | USPAT; US-PGPUB; EPO;<br>JPO; DERWENT;<br>IBM_TDB |
| 9  | BRS  | 16687  | sti or shallow adj trench  | USPAT; US-PGPUB; EPO;<br>JPO; DERWENT;<br>IBM_TDB |
| 10 | BRS  | 191069 | mosfet or (metal adj oxide adj semiconductor adj (fet<br>or field)) or pmos or cmos or nmos or misfet  | USPAT; US-PGPUB; EPO;<br>JPO; DERWENT;<br>IBM_TDB |

|    | Type | Hits | Search Text   | DBs   |
|----|------|------|---|---|
| 11 | BRS  | 80   | gate near2 (over or top or contact\$4) near2 (sti or shallow adj trench )   | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 12 | BRS  | 78   | (gate near2 (over or top or contact\$4) near2 (sti or shallow adj trench )) and (@ad < "20030714")  | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 13 | BRS  | 68   | (gate near2 (amorphous or alpha or undrop\$4 or intrinsic) near2 (polysilicon or polysi or poly adj (silicon or si)) and (sti or shallow adj trench )) and (@ad < "20030714") | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 14 | BRS  | 2210 | (sti or shallow adj trench).ti.   | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 15 | BRS  | 607  | (sti or shallow adj trench).ti.   | USPAT                                       |
| 16 | IS&R | 3083 | ((257/506) or (257/510) or (257/519) or (257/E21.546) or (438/435)).CCLS.   | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |